Silicon P-Channel MOS FET

HITACHI

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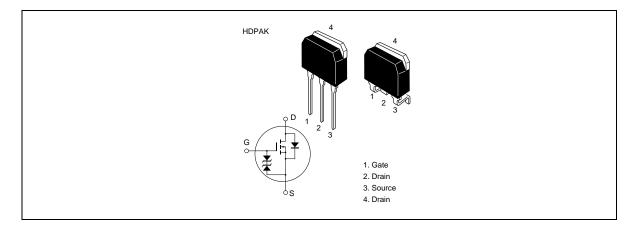
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device can be driven from 5 V source
- Suitable for Switching regulator, DC DC converter
- Avalanche Ratings

Outline



Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{dss}	-60	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	-50	А
Drain peak current	↓ *1 D(pulse)	-200	А
Body to drain diode reverse drain current	I _{DR}	-50	A
Avalanche current	*³	-50	A
Avalanche energy	E _{AR} * ³	214	mJ
Channel dissipation	Pch* ²	100	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes 1. $PW \le 10 \ \mu s$, duty cycle $\le 1\%$

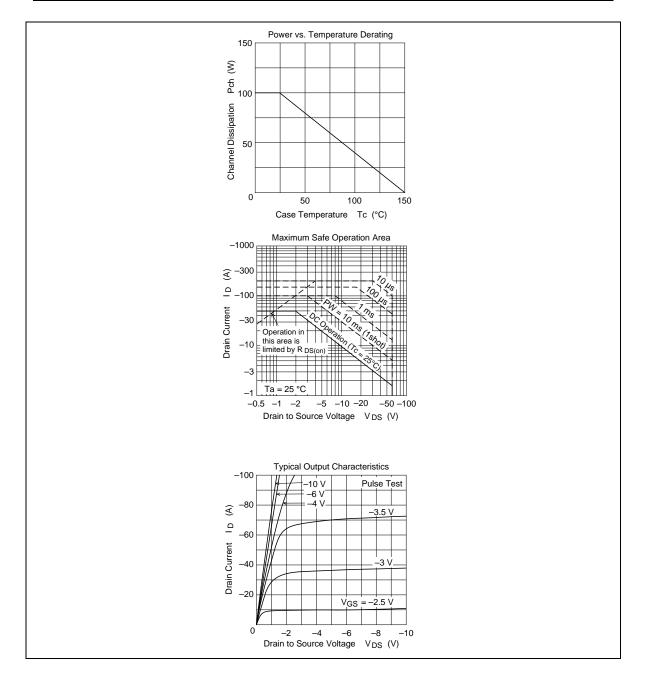
2. Value at Tc = 25°C

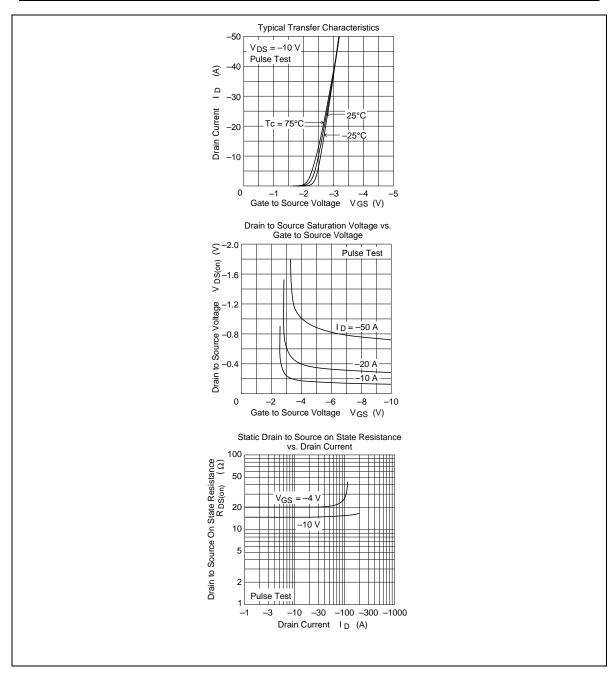
3. Value at Tch = 25°C, Rg \geq 50 Ω

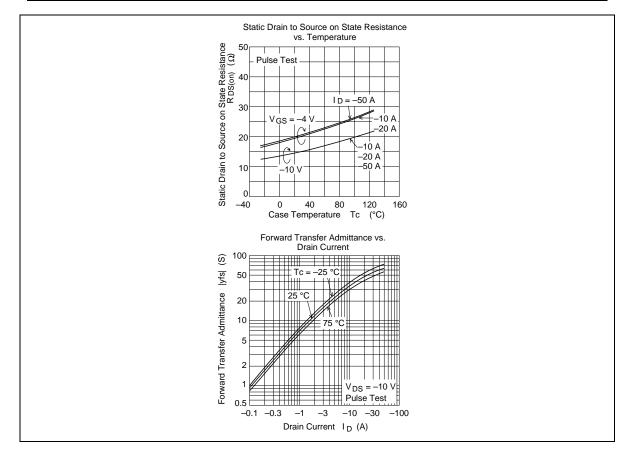
Electrical Characteristics (Ta = 25°C)

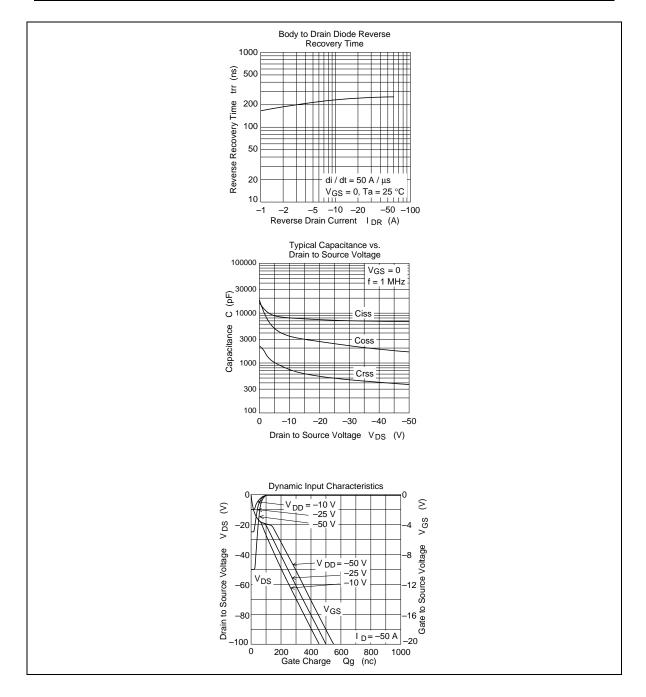
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{\scriptscriptstyle (BR)DSS}$	-60			V	$I_{_{D}} = -10 \text{ mA}, V_{_{GS}} = 0$
Gate to source breakdown voltage	$V_{\scriptscriptstyle (BR)GSS}$	±20	_	_	V	$I_{g} = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I _{GSS}	—		±10	μA	$V_{gs} = \pm 16 V, V_{ds} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	-250	μA	$V_{_{\rm DS}} = -50$ V, $V_{_{\rm GS}} = 0$
Gate to source cutoff voltage	$V_{\text{GS(off)}}$	-1.0	_	-2.25	V	$I_{\rm D} = -1 \text{ mA}, V_{\rm DS} = -10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	_	0.015	0.02	Ω	$I_{_{ m D}} = -25 \text{ A}$ $V_{_{ m GS}} = -10 \text{ V}^{*1}$
		_	0.02	0.028	Ω	$I_{D} = -25 \text{ A}$ $V_{GS} = -4 \text{ V}^{*1}$
Forward transfer admittance	y _{fs}	30	50	—	S	$I_{D} = -25 \text{ A}$ $V_{DS} = -10 \text{ V}^{*1}$
Input capacitance	Ciss	_	8200	_	pF	$V_{DS} = -10 V$ $V_{GS} = 0$ f = 1 MHz
Output capacitance	Coss	_	3650	_	pF	
Reverse transfer capacitance	Crss	_	750	_	pF	_
Turn-on delay time	t _{d(on)}	_	55	_	ns	$I_{D} = -25 \text{ A}$ $V_{GS} = -10 \text{ V}$ $R_{L} = 1.2 \Omega$
Rise time	t _r	_	340	_	ns	
Turn-off delay time	t _{d(off)}	—	1150	—	ns	_
Fall time	t _r	—	620	—	ns	
Body to drain diode forward voltage	V_{DF}	—	-1.0	—	V	$I_{_{\rm F}} = -50$ A, $V_{_{\rm GS}} = 0$
Body to drain diode reverse recovery time	t _{rr}	_	250		ns	$I_{F} = -50 \text{ A}, V_{GS} = 0,$ diF/dt = 50 A/µs
Note 1 Pulse Test						

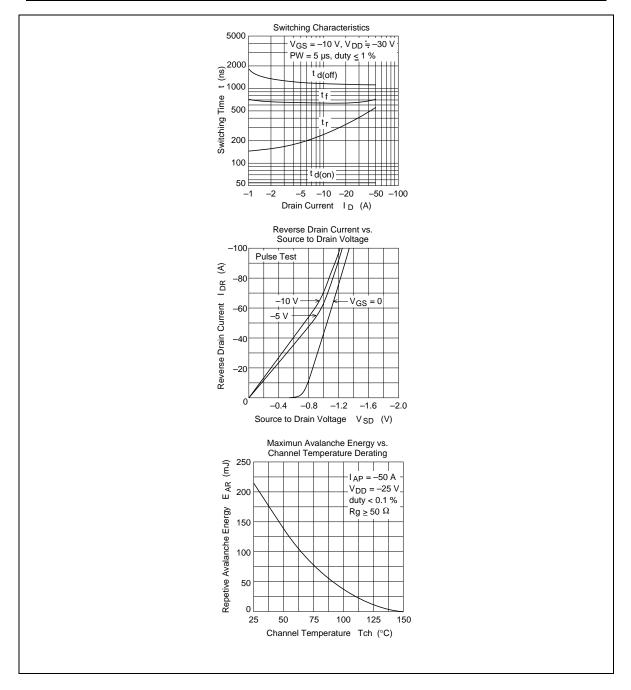
Note 1. Pulse Test

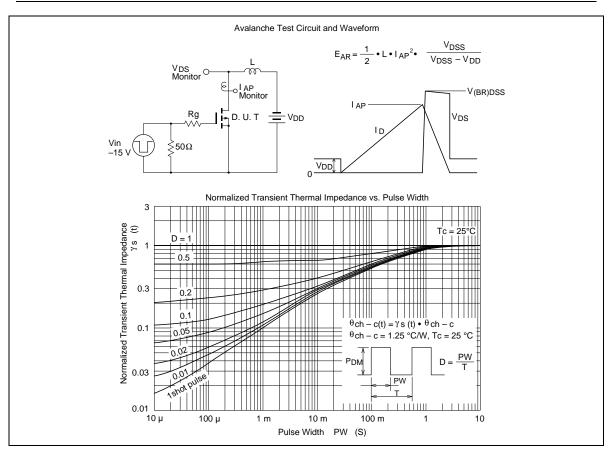












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